



Designing Oscillator for an Antenna at $\sim 3.5[GHz]$

2896

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Milestones completed so far

List of Milestones completed

- Selected the transistor we will use
- Simulated the oscillator we designed in PSpice
- Designed Matching network for the load(antenna)
- Optimised matching network for efficiency

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Choosing the BJT

Required characteristics

- The transistor needs high-frequency performance, including f_{\max} and f_t , well above 3.5[GHz].
- Low parasitic capacitance at collector, base, and emitter terminals is crucial.
- Low noise figure is essential.
- High gain, especially at the operating frequency, is necessary for stable oscillation.
- Ensure appropriate biasing for Colpitts oscillator operation, including DC voltages and currents.

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BFP520 from Infenion¹

- Surface mount low voltage silicon NPN RF bipolar transistor
- Transition frequency f_T of 45[GHz]
- High Gain, with $|S_{12}|$, G_{ma} , $G_{ms} > 16[dB]$ at 3.5[GHz] under $V_{ce} = 2[V]$
- Low Noise Figure, $NF < 1.2[dB]$ at 3.5[GHz], 2[V], 2[mA]

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Oscillator Circuit

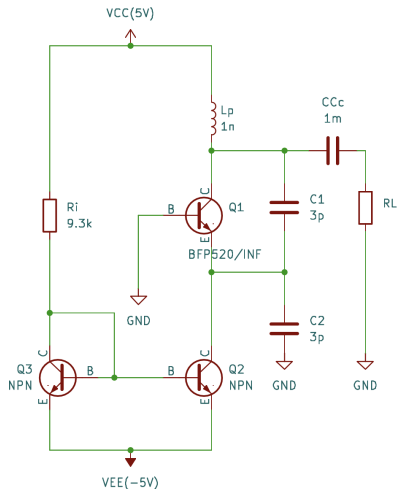
Collpit's Oscillator

- The circuit was tested with some high impedance load attached
- Values of L_p , C_1 and C_2 were computed using the operating frequency formula

$$f_c \approx \frac{1}{2\pi \sqrt{L_p \frac{C_1 C_2}{C_1 + C_2}}}$$

a

- $C_1 = C_2$ was chosen since it gave the highest oscillation frequency



^aIn-depth analysis in Appendix

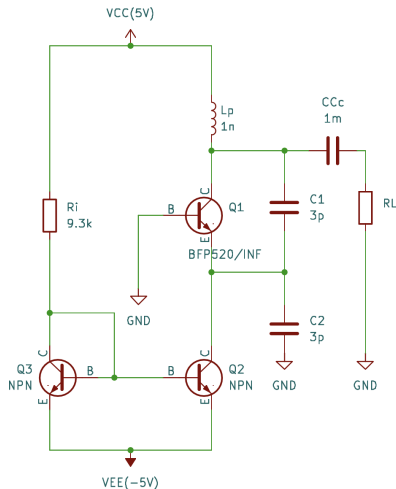
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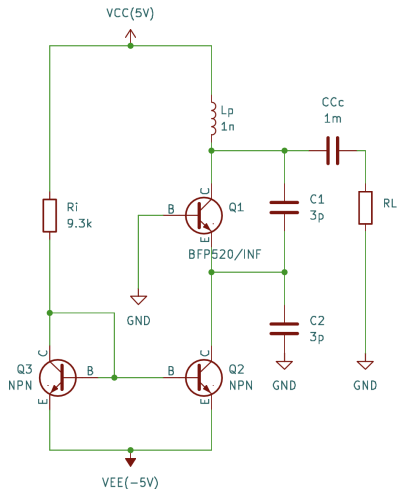
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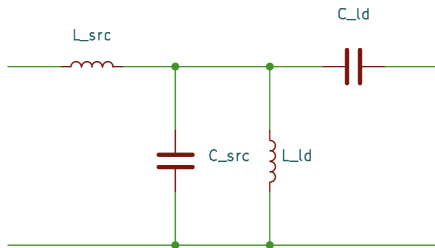
Output Waveform

Choosing a Matching Network

Matching Network

T-matching is better for matching a load to a source impedance when there's a large disparity because it provides efficient power transfer, minimizes losses, and offers impedance transformation with stability.²

- $L_{src} =$
- $C_{src} =$
- $L_{ld} =$
- $C_{ld} =$



²Design method in Appendix

S-parameters of the Matching Network

Tested with $R_S = 1000[\Omega]$ and $R_L = 50[\Omega]$

Output of Oscillator using Matching Network as $50[\Omega]$ load



Efficiency η

Calculation of η

- **Input:** $P_{DC} = V_{CC}I_C$
- **Output:** $P_{ac} = \frac{V_{rms}^2}{R_L}$ where $V_{rms} = \frac{V_{max}}{\sqrt{2}}$ for the output waveform
- **Efficiency:** $\eta = \frac{P_{ac}}{P_{DC}}$ ³

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We have $\eta \approx 11\%$

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- Measure S-parameters of the antenna and of the whole system
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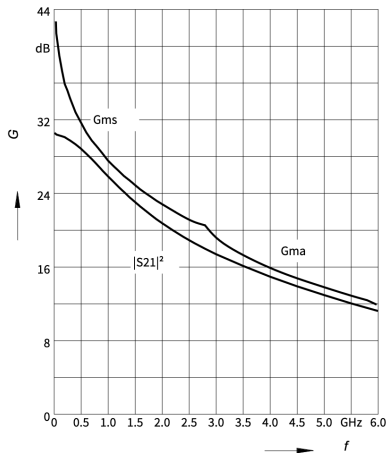
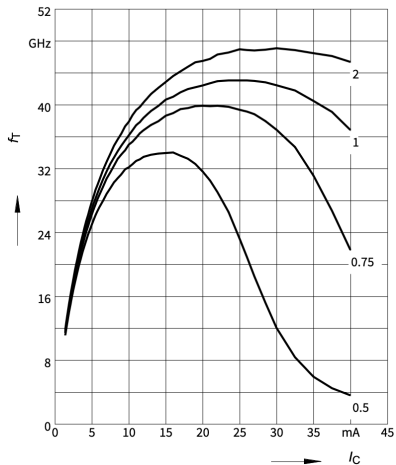
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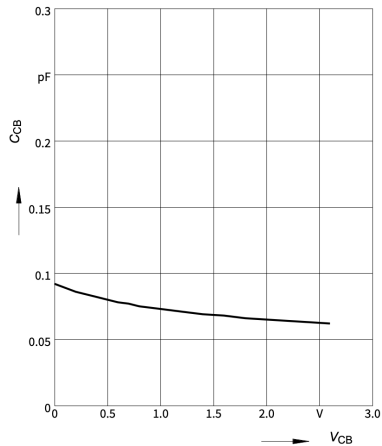
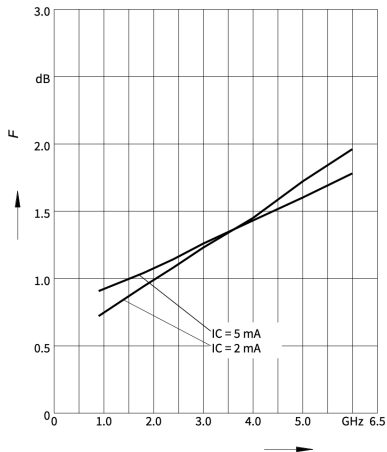
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Appendix

Data from Infenion - 1



Data from Infenion - 2



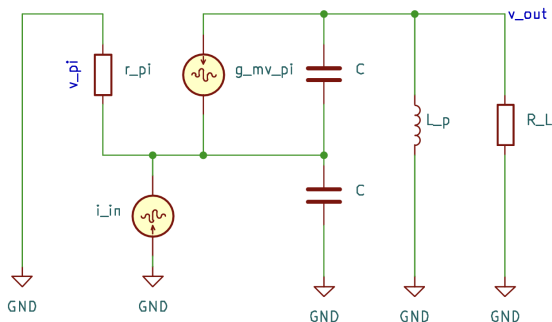
BFP520 Spice File

```
*$
.SUBCKT BFP520/INF 200 100 300
L1      1      10      0.47nH
L2      2      20      0.56nH
L3      3      30      0.23nH
C1      10     20      6.9fF
C2      20     30      134fF
C3      30     10      136fF
L4      10     100     0.53nH
L5      20     200     0.58nH
L6      30     300     0.05nH
Q1      2 1 3 BFP520
.ENDS
.MODEL BFP520 NPN(
+ IS =1.5E-17      NF =1      NR =1
+ ISE=2.5E-14      NE =2      ISC=2E-14
+ NC =2            BF =235    BR =1.5
+ VAF=25           VAR=2      IKF=0.4
+ IKR=0.01         RB =11     RBM=7.5
+ RE =0.6          RC =7.6     CJE=2.35E-13
+ VJE=0.958        MJE=0.335   CJC=9.3E-14
+ VJC=0.661        MJC=0.236   CJS=0
+ VJS=0.75         MJS=0.333   FC=0.5
+ XCJC=1           TF=1.7E-12   TR=5E-08
+ XTF=10           ITF=0.7      VTF=5
+ PTF=50           XTB=-0.25    XTI=0.035
+ EG=1.11)
*****
```

*\$

Proof of operating frequency - 1

We have the following small signal model of Collpit's oscillator, with $C_1 = C_2 = C^4$



⁴In all the results, we try to ignore effects of r_{π} and then adjust the values accordingly to get required response

Proof of operating frequency - 2

$$i_{in} = -\frac{v_{\pi}}{r_{\pi}} - sC(v_{out} + 2v_{\pi})$$

$$g_m v_{\pi} + sC(v_{out} + v_{\pi}) + \frac{v_{out}}{sL_p} + \frac{v_{out}}{R_L} = 0$$

This gives us the following frequency response

$$\frac{v_{out}}{i_{in}} = \frac{r_{\pi} L_p R_L (s^2 C + s g_m)}{r_{\pi} C^2 L_p R_L s^3 + (-r_{\pi} C L_p R_L g_m + 2r_{\pi} C L_p + C L_p R_L) s^2 + (2r_{\pi} C R_L + L_p) s + R_L}$$

Put $s = j\omega$ and let Im of denominator $\rightarrow 0$

$$\omega_0 = \sqrt{\frac{2r_{\pi} C R_L + L_p}{r_{\pi} C^2 L_p R_L}}$$

Assuming $r_{\pi} \rightarrow \infty$, as is the case is MOS, we reach the well-known expression $\omega_0 = \sqrt{\frac{1}{L \frac{C \cdot C}{C+C}}}$

Proof of operating frequency - 3

For sustained oscillations, we need

$$-(-r_{\pi}CL_pR_Lg_m + 2r_{\pi}CL_p + CL_pR_L)\omega_0^2 + R_L > 0$$

This gives us

$$^5R_Lg_m - \frac{R_L}{r_{\pi}} - 2 > 0$$

Thus, we need to set R_L accordingly at the oscillating frequency, giving us a lower bound for load and thus a need for a matching network.

⁵This is similar to the condition found in Razavi, but for NMOS in place of NPN BJT

Calculation of matching network - 1

We have a source impedance Z_s , a load impedance Z_L , and operating frequency f_0 and we need to match Z_L to Z_s at f_0 using a T-Matching Network. We assume a central impedance Z_c such that $Z_c > \max(Z_s, Z_L)$, and then calculate the series and parallel reactive components on both sides.⁶

Source:

$$Q_{src} = \sqrt{\frac{Z_c}{Z_s} - 1}$$

$$X_{src}^{parallel} = \frac{Z_c}{Q_{src}}$$

$$X_{src}^{series} = Q_{src} Z_s$$

Load:

$$Q_{ld} = \sqrt{\frac{Z_c}{Z_L} - 1}$$

$$X_{ld}^{parallel} = \frac{Z_c}{Q_{ld}}$$

$$X_{ls}^{series} = Q_{ls} Z_L$$

Then, $L = \frac{X}{2\pi f_0}$ and $C = \frac{1}{2\pi f_0 X}$ for chosen X series/parallel





⁶In our case, all impedances are real



Calculation of matching network - 2

Variable	Value
f_0	3.5×10^9
$Z_{\text{out_osc}}$	1000
Z_{load}	50
Z_{center}	1002
Q_{src}	0.0447214
$X_{\text{paralle_src}}$	22405.4
$X_{\text{series_src}}$	44.7214
L_{src}	2.03361×10^{-9}

Variable	Value
C_{src}	2.02955×10^{-15}
Q_{ld}	4.36348
$X_{\text{paralle_ld}}$	229.633
$X_{\text{series_ld}}$	218.174
L_{ld}	1.04421×10^{-8}
C_{ld}	2.08424×10^{-13}
C_{com}	2.10454×10^{-13}
L_{com}	1.70212×10^{-9}

References i

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